

FEATURES

- Rack mounted system
- Class AB linear GaAs FET design
- Instantaneous wide bandwidth
- Suitable for all single channel modulation standards
- Built-in protection circuits
- High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	6.0 - 18.0GHz	
Power Output @ Psat	20 Watt Min	CW
Power Gain	43 dB Min	
Power Gain Flatness	4.0 dB p-p Max	
Input Return Loss	10 dB Min	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	33dBm/Tone, Δ = 1MHz
Harmonics 2 nd /3 rd	-15 / -20 dBc Typ	At rated Pout
Non Harmonics Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	300 Watt Max	At rated Pout
Max Input Power protection	+5 dBm	<10 Seconds
Load VSWR Protection	5 : 1	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50°C	
Storage Temperature	-20 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 88 x 562 mm	2U
Weight	9 kg.	
RF Connectors In/Out	SMA Female	Front Panel Standard
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485 Optional GPIB Interface	Optional Remote Bluetooth application

OUTLINE DRAWING

